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Amendments to the Claims:

Please amend Claims 1, 6, 14, 17, 19, and 22 as indicated in the following listing of claims, which replaces all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A method for depositing a film on a substrate wafer disposed within a process chamber, the method comprising:
providing a first gaseous mixture to the process chamber;
inductively generating a plasma from the first gaseous mixture with a toroidal plasma source ~~disposed within the process chamber~~ to deposit a first portion of the film on the substrate wafer, the toroidal plasma source being disposed within the process chamber and comprising a core and a coil;
thereafter, flowing an etchant gas into the process chamber without terminating the plasma to provide a net etching back of part of the first portion of the film; and
thereafter, providing a second gaseous mixture to the process chamber without terminating the plasma to deposit a second portion of the film on the substrate wafer.
2. (Original) The method recited in claim 1 further comprising applying an electrical bias to the substrate while flowing the etchant gas.
3. (Original) The method recited in claim 2 wherein the bias has a power density approximately between 0.9 W/cm^2 and 3.2 W/cm^2 .
4. (Original) The method recited in claim 1 wherein the second gaseous mixture is substantially the same as the first gaseous mixture.